FIELD EMISSION FROM SINGLE AND FEW-LAYER GRAPHENE FLAKES

 $\begin{array}{l} \textbf{S. Santandrea}^{a}, \textbf{F. Giubileo}^{a}, \underline{\textbf{V. Grossi}^{b}}, \\ \textbf{S. Santucci}^{b}, \textbf{M. Passacantando}^{b}, \textbf{T. Schroeder}^{c}, \\ \textbf{G. Lupina}^{c} \text{ and } \textbf{A. Di Bartolomeo}^{a} \end{array}$

^aDipartimento di Fisica, Centro NANO_MATES, Università degli Studi di Salerno, and CNR-SPIN Salerno, via Ponte don Melillo, 84084 Fisciano (SA), Italy ^bDipartimento di Fisica, Università degli Studi dell'Aquila, via Vetoio, 67100 Coppito, LAquila, Italy ^cIHP, Im Technologiepark 25, 15236 Frankfurt (Oder), Germany

Graphene, consisting of a single- or few-graphite layers, has a very high aspect ratio (thickness to lateral size ratio) and a dramatically enhanced local electric field is expected at its edges; it shares many similar or even superior properties as carbon nanotubes (CNTs) and, as CNTs, has high potentiality for field emission (FE) applications [1-3]. So far, most of the work has been performed on graphene films [4,5] or on graphene/polymer composites [6] reporting FE from graphene edges or pleats at low applied fields; no observation of FE current from the inner, flat part of graphene flakes has been reported [7]. We report observation of FE current from the inner, flat part of single-and few- layer graphene flakes, which can make the fabrication of graphene based cathodes easier for FE applications [8].

Single- and few-layer graphene sheets were prepared by mechanical exfoliation of highly ordered pyrolytic graphite and transferred by scotch-tape method on SiO₂ layer thermally grown on p-type Si substrate. The thickness of the SiO₂ layer was chosen to \sim 300 nm. Raman spectroscopy was further exploited to give confirmation of the single- or few-layer graphene. Taking advantage of a special setup, consisting of a two-probe nanomanipulation system (two tungsten tips with curvature radius <100 nm) operating in a scanning electron microscope (SEM) and connected to external source measurement units (SMUs), we investigate FE currents by applying electric fields up to 2 kV/ μ m. The tips, one in contact with graphene and the second at a varying distance from it, were used as the cathode and the anode, respectively.

We show that a high and stable FE current (up to 1 μ A), well described by the usual FowlerNordheim (FN) model over five orders of magnitude, can be achieved with a turn-on field of ~600 V/ μ m. This high field is not surprising since the electrons are emitted from a flat surface, which do not benefit from the high field enhancement factor of a tiplike shape. We tested also the emission stability from the flat inner part of single-layer graphene flake, due to its relevance for practical applications. Experimentally, we applied a constant bias and monitored the current over periods of several hours, over which a stable process was confirmed.

References

- [1] W. A. de Heer et al., Science, 270 (1995) 1179.
- [2] M. Passacantando et al., Nanotechnology, 19 (2008) 395701.
- [3] A. Di Bartolomeo et al., Carbon, 45 (2007) 2957.
- [4] S. W. Lee et al., Nanoscale Res. Lett., 4 (2009) 1218.
- [5] J. Liu et al., Appl. Phys. Lett., 97 (2010) 033109.
- [6] G. Eda et al., H. Unalan, Appl. Phys. Lett., 93 (2008) 233502.
- [7] Z. Xiao et al., ACS Nano, 4 (2010) 6332.
- [8] S. Santandrea et al., Appl. Phys. Lett., 98 (2011) 163109.